

In the Claims:

1. (Currently amended) A process for the fabrication of
2 isolation structures with the following process steps
3 [[●]] provision of a semiconductor substrate (11),
4 [[●]] forming of at least two trenches (12) spaced from each
5 other in the semiconductor substrate (11) with at
6 least one rib (13) positioned between the
7 trenches (12),
8 [[●]] conversion of the substrate material in the area of
9 the trenches (12) into an electrically insulating
10 material (14) up to the complete conversion of
11 the rib or the ribs (13) arranged between them,
12 [[●]] forming of a functional structure (15) within the
13 substrate material which is mechanically
14 connected with the substrate exclusively by means
15 of the converted substrate material which is
16 formed at the trenches.
1. 2. (Previously presented) A process according to claim 1,
2 characterized in that silicon is used as semiconductor
3 substrate.
1. 3. (Previously presented) A process according to claim 2,
2 characterized in that the substrate material is converted
3 by means of thermal oxidation.

Claims 4, 5, 6 (Canceled).

1 7. (Previously presented) A process according to claim 1,
2 characterized in that a continuous insulating oxide
3 structure (14) over longer distances is created by means of
4 a continuous arrangement of trenches (12) and ribs (13)
5 between them.

1 8. (Previously presented) A process according to claim 1,
2 characterized in that with greater widths of the ribs (13),
3 the process step of conversion is a multi-step process.

1 9. (Previously presented) A process according to claim 8,
2 characterized in that after a first process step of the
3 conversion, the so created converted material is removed
4 and thereafter the remaining material is converted in a
5 second process step of the conversion.